The Raw Silicon Wafer

3-inch mono crystal silicon N-type light doped wafer

Resistivity Ω·CM	Thickness μm	Crystal Orientation	Lifeμs	External Diametermm	Dopant	Form				Radial inhomogeneity of resistivity
						Line Slice	Grind	Chamfering Film	Positioning Piece	
5-10	200-350	〈111〉	＞100	76.2±0.3	Phosphorus	√	√	√	√	≤20%
10-15	200-350	〈111〉	＞100	76.2±0.3	Phosphorus	√	√	√	√	≤20%
15-20	200-350	〈111〉	＞100	76.2±0.3	Phosphorus	√	√	√	√	≤20%
20-25	200-350	〈111〉	＞100	76.2±0.3	Phosphorus	√	√	√	√	≤20%
25-30	200-350	〈111〉	＞100	76.2±0.3	Phosphorus	√	√	√	√	≤20%
30-35	200-350	〈111〉	＞100	76.2±0.3	Phosphorus	√	√	√	√	≤20%
35-40	200-350	〈111〉	＞100	76.2±0.3	Phosphorus	√	√	√	√	≤20%
40-45	200-350	〈111〉	＞100	76.2±0.3	Phosphorus	√	√	√	√	≤20%
45-50	200-350	〈111〉	＞100	76.2±0.3	Phosphorus	√	√	√	√	≤20%
50-55	200-350	〈111〉	＞100	76.2±0.3	Phosphorus	√	√	√	√	≤20%

4-inch mono crystal silicon N-type light doped wafer

Resistivity Ω·CM	Thickness μm	Crystal Orientation	Lifeμs	External Diametermm	Dopant	Form				Radial inhomogeneity of resistivity
						Line Slice	Grind	Chamfering Film	Positioning Piece	
5-10	200-350	〈111〉	＞100	101.6±0.3	Phosphorus	√	√	√	√	≤20%
10-15	200-350	〈111〉	＞100	101.6±0.3	Phosphorus	√	√	√	√	≤20%
15-20	200-350	〈111〉	＞100	101.6±0.3	Phosphorus	√	√	√	√	≤20%
20-25	200-350	〈111〉	＞100	101.6±0.3	Phosphorus	√	√	√	√	≤20%
25-30	200-350	〈111〉	＞100	101.6±0.3	Phosphorus	√	√	√	√	≤20%
30-35	200-350	〈111〉	＞100	101.6±0.3	Phosphorus	√	√	√	√	≤20%
35-40	200-350	〈111〉	＞100	101.6±0.3	Phosphorus	√	√	√	√	≤20%
40-45	200-350	〈111〉	＞100	101.6±0.3	Phosphorus	√	√	√	√	≤20%
45-50	200-350	〈111〉	＞100	101.6±0.3	Phosphorus	√	√	√	√	≤20%
50-55	200-350	〈111〉	＞100	101.6±0.3	Phosphorus	√	√	√	√	≤20%

3-inch mono crystal silicon heavy doped wafer

Resistivity Ω·CM	Thickness μm	Crystal Orientation	Model	External Diametermm	Dopant	Form				Radial inhomogeneity of resistivity
						Line Slice	Grind	Chamfering Film	Positioning Piece	
0.003-0.005	200-350	〈111〉	N/P	76.2±0.3	Phosphorus /Boron	/	√	√	√	/
0.005-0.008	200-350	〈111〉	N/P	76.2±0.3	Phosphorus /Boron	/	√	√	√	/
0.02-0.03	200-350	〈111〉	N/P	76.2±0.3	Phosphorus /Boron	/	√	√	√	/

4 inch monocrystal silicon heavy doped wafer

						Form	Radial